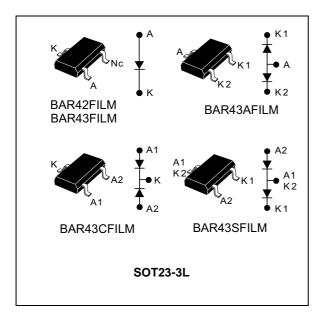


BAR42 BAR43

Small signal Schottky diode

Datasheet - production data



Description

General purpose metal to silicon diodes featuring very low turn-on voltage and fast switching.

Table 1. Device summary				
Symbol	Value			
I _{F(AV)}	0.1 A			
V _{RRM}	30 V			
Тj	150 °C			
V _F (max)	0.33 and 0.40 V			

Features

- Very small conduction losses
- Negligible switching losses
- Low forward voltage drop
- Surface mount device

This is information on a product in full production.

1 Characteristics

Parameter	Value	Unit	
Repetitive peak off-state voltage	30	V	
Continuous forward current	Continuous forward current		
Surge non repetitive forward current	0.75	А	
Power dissipation ⁽¹⁾	250	mW	
Maximum Storage temperature range	- 65 to + 150	°C	
Maximum operating junction temperature ⁽	150	°C	
Maximum temperature for soldering during	260	°C	
	Repetitive peak off-state voltage Continuous forward current Surge non repetitive forward current Power dissipation ⁽¹⁾ Maximum Storage temperature range Maximum operating junction temperature ⁽	Repetitive peak off-state voltageContinuous forward currentSurge non repetitive forward current $t_p = 10 \text{ ms sinusoidal}$ Power dissipation ⁽¹⁾ $T_{amb} = 25 \ ^{\circ}C$	Repetitive peak off-state voltage30Continuous forward current0.1Surge non repetitive forward current $t_p = 10 \text{ ms sinusoidal}$ 0.75Power dissipation ⁽¹⁾ $T_{amb} = 25 \text{ °C}$ 250Maximum Storage temperature range- 65 to + 150Maximum operating junction temperature ⁽²⁾ 150

Table 2. Absolute ratings (limiting values)

1. For double diodes, P_{tot} is the total dissipation of both diodes

2. $\frac{dPtot}{dT_j} < \frac{1}{Rth(j-a)}$ condition to avoid thermal runaway for a diode on its own heatsink.

Table 3. Thermal parameter

Symbol	Parameter	Value	Unit
R _{th(j-a)}	Junction to ambient ⁽¹⁾	500	°C/W

1. Mounted on epoxy board with recommended pad layout.

Symbol	Parameter	Test conditions			Min.	Тур.	Max.	Unit
V_{BR}	Breakdown voltage	T _j = 25 °C		I _R = 100 μA	30			V
I _R ⁽¹⁾	Reverse leakage	$T_j = 25 \text{ °C}$ $T_j = 100 \text{ °C}$		V _R = V _{RRM}			500	nA
^{IR} `´ C	current						100	μA
	Forward voltage drop	T _j = 25 °C	BAR42	I _F = 10 mA		0.35	0.40	
				I _F = 50 mA		0.50	0.65	
			BAR43	$I_F = 2 \text{ mA}$	0.26		0.33	V
				I _F = 15 mA			0.45	
			ALL	I _F =100 mA			1	

Table 4. Static electrical characteristics

1. Pulse test: t_p = 5 ms, δ < 2 %

2. Pulse test: t_p = 380 µs, δ < 2 %

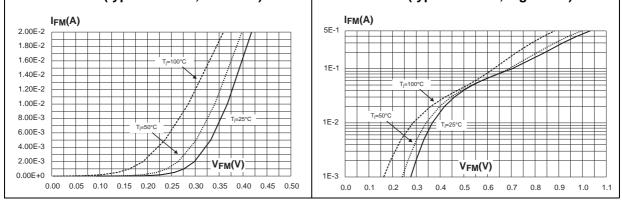


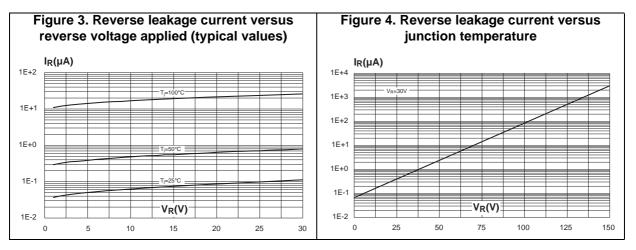
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Table 5. Dynamic characteristics (1) = 25° C)						
Symbol	Test conditions			Тур.	Max.	Unit
С	Junction capacitance	$T_j = 25 \text{ °C}$ $V_R = 1 \text{ V}$ $F = 1 \text{ MHz}$		7		рF
С	Reverse recovery time	$ I_F = 10 \text{ mA} I_R = 10 \text{ mA} \\ T_j = 25 \text{ °C} I_{rr} = 1 \text{ mA} R_L = 100 \Omega $			5	pF
η	Detection efficiency	$\begin{array}{l} C_{L} = 300 \; pF F = 45 \; MHz \\ T_{j} = 25 \; ^{\circ} C V_{i} = 2 \; V R_{L} = 50 \; \Omega \end{array}$	80			ps

Table 5. Dynamic characteristics (Tj = 25 °C)









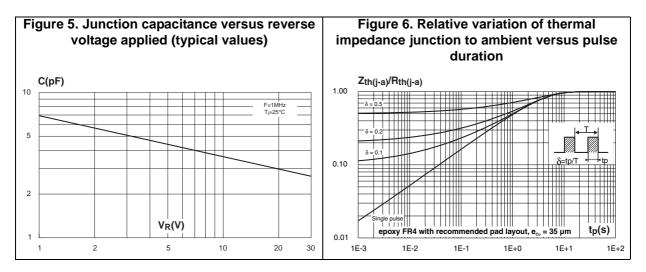
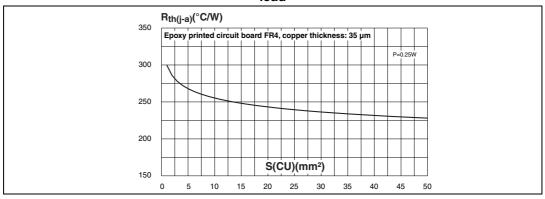


Figure 7. Thermal resistance junction to ambient versus copper surface under each lead





2 Package information

- Epoxy meets UL94, V0
- Lead-free packages

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: <u>www.st.com</u>. ECOPACK[®] is an ST trademark.

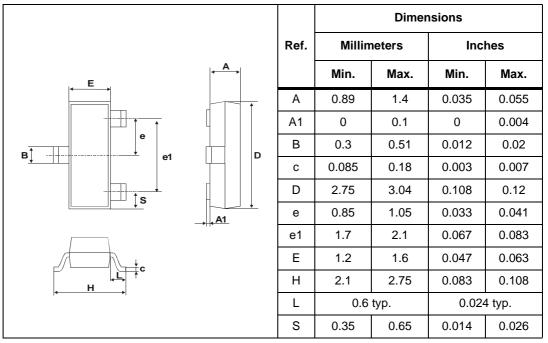
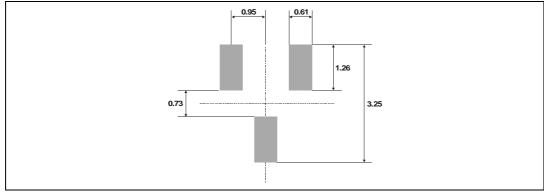


Table 6. SOT23-3L dimensions

Figure 8. Footprint (dimensions in mm)





3 Ordering information

Order code	Marking	Package	Weight	Base Qty	Delivery mode
BAR42FILM	D94				
BAR43FILM	D95				
BAR43AFILM	DB1	SOT23-3L	0.01 g	3000	Tape and reel
BAR43CFILM	DB2				
BAR43SFILM	DA5				

Table 7. Ordering information

4 Revision history

Date	Revision	Changes
Aug-2001	2B	Last release.
16-Apr-2005	3	Layout update. No content change.
23-Apr-2014	4	Updated ECOPACK statement.
18-Jul-2017	5	Updated figure in cover page.

 Table 8. Document revision history



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DocID3288 Rev 5